

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Avalanche characteristic.
2. High current, low forward voltage.
3. High frequency, Fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. X-ray power supply.

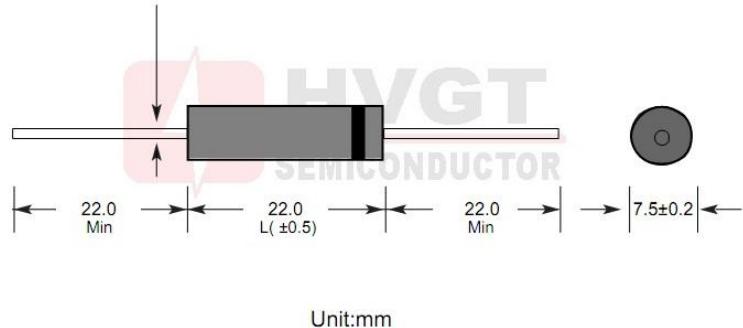
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.55 grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm)
HVGT NAME: DO-722
DO-722 Series

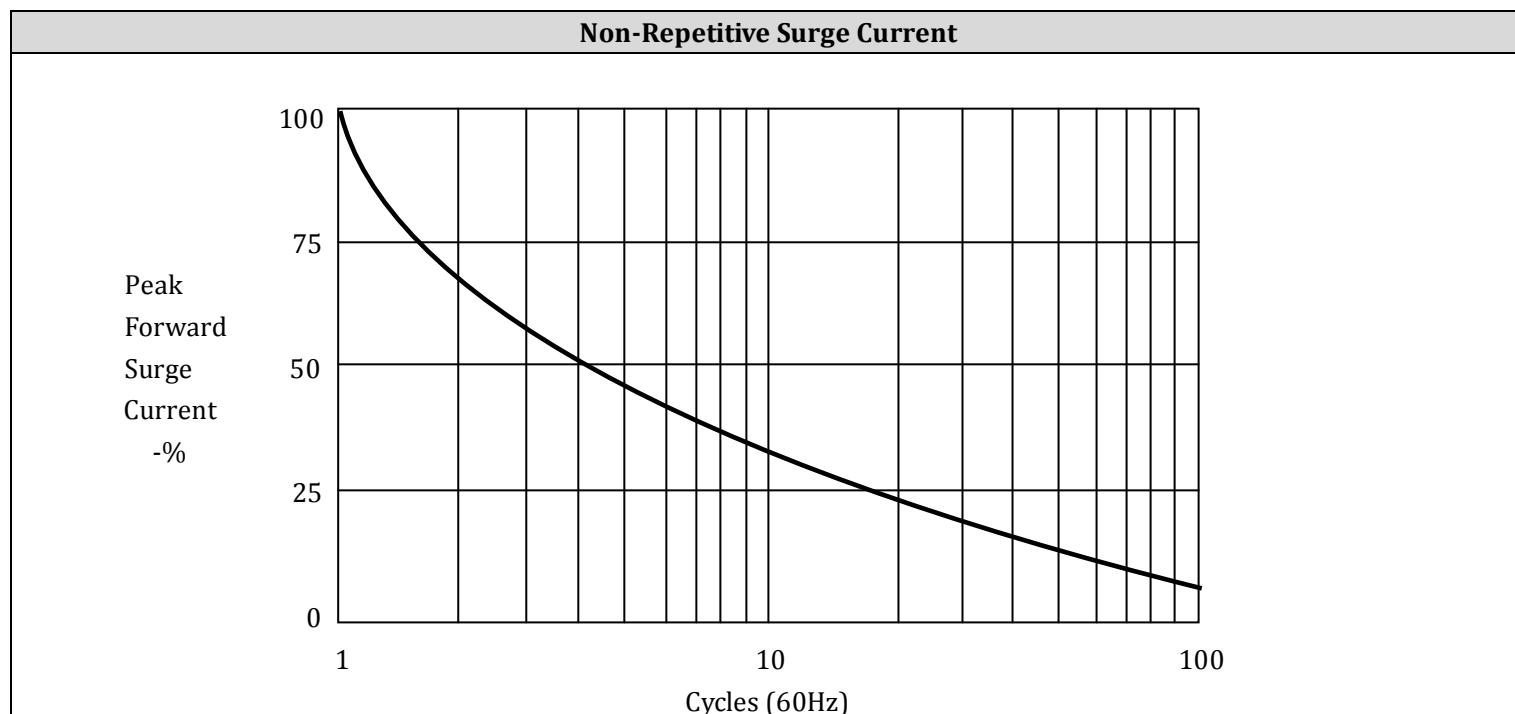
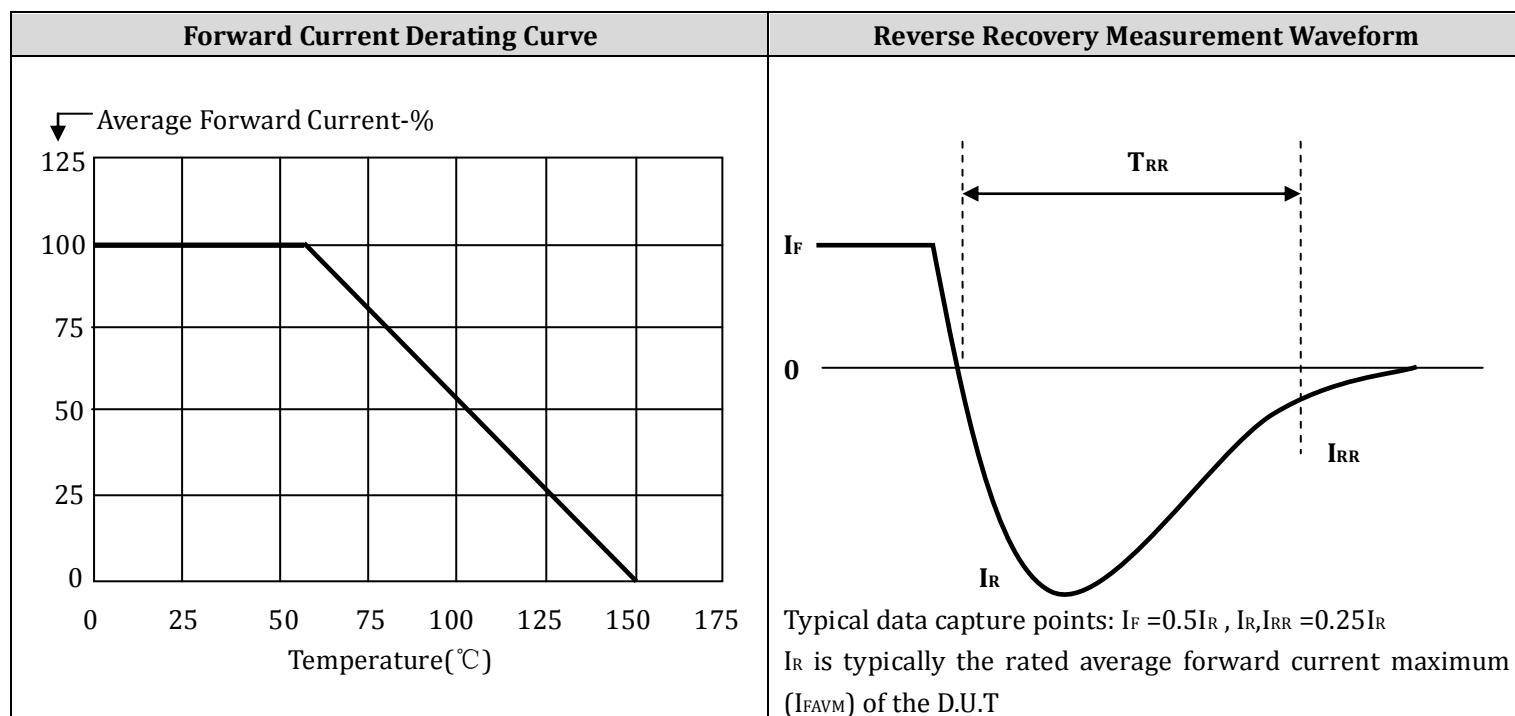
Lead Diameter 1.2mm ±0.02


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}	T _A =25°C	4.0	kV
Non-Repetitive Peak Reverse Voltage	V _{RSM}	T _A =25°C	--	kV
Average Forward Current Maximum	I _{FAVM}	T _A =55°C	3.5	A
		T _{OIL} =55°C	--	A
Non-Repetitive Forward Surge Current	I _{FSM}	T _A =25°C; 60Hz Half-Sine Wave; 8.3mS	70	A
Junction Temperature	T _J		150	°C
Allowable Operation Case Temperature	T _C		-40~+150	°C
Storage Temperature	T _{STG}		-40~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V _{FM}	at 25°C; at I _{FAVM}	4.8	V
Maximum Reverse Current	I _{R1}	at 25°C; at V _{RRM}	2.0	uA
	I _{R2}	at 100°C; at V _{RRM}	10	uA
Maximum Reverse Recovery Time	T _{RR}	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	150	nS
Junction Capacitance	C _J	at 25°C; V _R =0V; f=1MHz	--	pF



Marking	Type	Code	Cathode Mark
	ESJW04	ESJW04 HVGT	